

# OKI semiconductor

## MSM271024AS

65536 × 16 BIT UV ERASABLE ELECTRICALLY PROGRAMMABLE  
READ-ONLY MEMORY

### GENERAL DESCRIPTION

The MSM271024 is a 65536 words × 16 bit ultraviolet erasable and electrically programmable read-only memory. Users can freely prepare the memory content, which can be easily changed, so the MSM271024 is ideal for microprocessor programs, etc. The MSM271024 is manufactured by the N channel double silicon gate MOS technology and is contained in the 40 pin package.

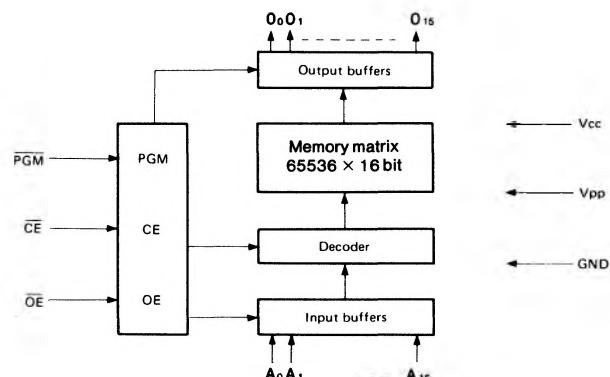
### FEATURES

- +5V single power supply
- 65536 words × 16 bit configuration
- Access time:
  - MAX120 ns (MSM271024-12)
  - MAX150 ns (MSM271024-15)
  - MAX200 ns (MSM271024-20)
- Power consumption:
  - MAX525 mW (during operation)
  - MAX184 mW (during stand-by)
- Perfect static operation
- INPUT/OUTPUT TTL level  
(three state output)

### PIN CONFIGURATION

V <sub>pp</sub>	1	40	V <sub>CC</sub>
CE	2	39	PGM
O <sub>15</sub>	3	38	NC
O <sub>14</sub>	4	37	A <sub>15</sub>
O <sub>13</sub>	5	36	A <sub>14</sub>
O <sub>12</sub>	6	35	A <sub>13</sub>
O <sub>11</sub>	7	34	A <sub>12</sub>
O <sub>10</sub>	8	33	A <sub>11</sub>
O <sub>9</sub>	9	32	A <sub>10</sub>
O <sub>8</sub>	10	31	A <sub>9</sub>
V <sub>SS</sub>	11	30	V <sub>SS</sub>
O <sub>7</sub>	12	29	A <sub>8</sub>
O <sub>6</sub>	13	28	A <sub>7</sub>
O <sub>5</sub>	14	27	A <sub>6</sub>
O <sub>4</sub>	15	26	A <sub>5</sub>
O <sub>3</sub>	16	25	A <sub>4</sub>
O <sub>2</sub>	17	24	A <sub>3</sub>
O <sub>1</sub>	18	23	A <sub>2</sub>
O <sub>0</sub>	19	22	A <sub>1</sub>
OE	20	21	A <sub>0</sub>

### FUNCTIONAL BLOCK DIAGRAM



This specification may be changed without notification.

**FUNCTION TABLE**

Pins Mode	$\overline{\text{CE}}$ (2)	$\overline{\text{OE}}$ (20)	$\overline{\text{PGM}}$ (39)	V <sub>pp</sub> (1)	V <sub>CC</sub> (40)	Outputs
Read	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	+5V	+5V	Dout
Output Disable	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	+5V	+5V	High impedance
Stand-by	V <sub>IH</sub>	—	—	+5V	+5V	High impedance
Program	V <sub>IL</sub>	—	V <sub>IL</sub>	+12.5V	+6V	D <sub>i</sub> N
Program Verify	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	+12.5V	+6V	Dout
Program Inhibit	V <sub>IH</sub>	—	—	+12.5V	+6V	High impedance

—; Can be either V<sub>IL</sub> or V<sub>IH</sub>**ABSOLUTE MAXIMUM RATINGS**

Temperature Under Bias	T <sub>a</sub> . . . . .	-10°C ~ 80°C
Storage Temperature	T <sub>stg</sub> . . . . .	-55°C ~ 125°C
All Input/Output Voltages	V <sub>IN</sub> , V <sub>OUT</sub> . . . . .	-0.6V ~ 13V
V <sub>CC</sub> Supply Voltage	V <sub>CC</sub> . . . . .	-0.3V ~ 7V
Program Voltage	V <sub>pp</sub> . . . . .	-0.6V ~ 13.5V
Power Assembly Voltage	P <sub>D</sub> . . . . .	1.5W

The voltage with respect to GND.

**ELECTRICAL CHARACTERISTICS****<READ OPERATION>****RECOMMENDED OPERATION CONDITION**

Parameter	Symbol	Limit			Operating Temperature	Remarks	
		Min.	Typ.	Max.			
V <sub>CC</sub> Power Supply Voltage	V <sub>CC</sub>	4.75	5.0	5.25	0°C ~ 70°C	V <sub>CC</sub> =5V±0.25V V <sub>pp</sub> =V <sub>CC</sub>	V
V <sub>pp</sub> Voltage	V <sub>pp</sub>	4.75	5.0	5.25			V
"H" Level Input Voltage	V <sub>IH</sub>	2.00	—	6.25			V
"L" Level Input Voltage	V <sub>IL</sub>	-0.1	—	0.8			V

The voltage with respect to GND

**DC CHARACTERISTICS**(V<sub>CC</sub> = 5V ± 5%, V<sub>PP</sub> = V<sub>CC</sub>, Ta = 0°C ~ 70°C)

Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Input Leakage Current	I <sub>LI</sub>	V <sub>IN</sub> = 5.25V	—	—	10	μA
Output Leakage Current	I <sub>LO</sub>	V <sub>OUT</sub> = 5.25V	—	—	10	μA
V <sub>CC</sub> Power Current (Stand-by)	I <sub>CC1</sub>	CĒ = V <sub>IH</sub>	—	—	35	mA
V <sub>CC</sub> Power Current (Operation)	I <sub>CC2</sub>	CĒ = V <sub>IL</sub>	—	—	100	mA
Program Power Current	I <sub>PP1</sub>	V <sub>PP</sub> = V <sub>CC</sub>	—	—	5	mA
Input Voltage "H" Level	V <sub>IH</sub>	—	2.0	—	V <sub>CC</sub> +1	V
Input Voltage "L" Level	V <sub>IL</sub>	—	-0.1	—	0.8	V
Output Voltage "H" Level	V <sub>OH</sub>	I <sub>OH</sub> = -400 μA	2.4	—	—	V
Output Voltage "L" Level	V <sub>OL</sub>	I <sub>OL</sub> = 2.1 mA	—	—	0.45	V

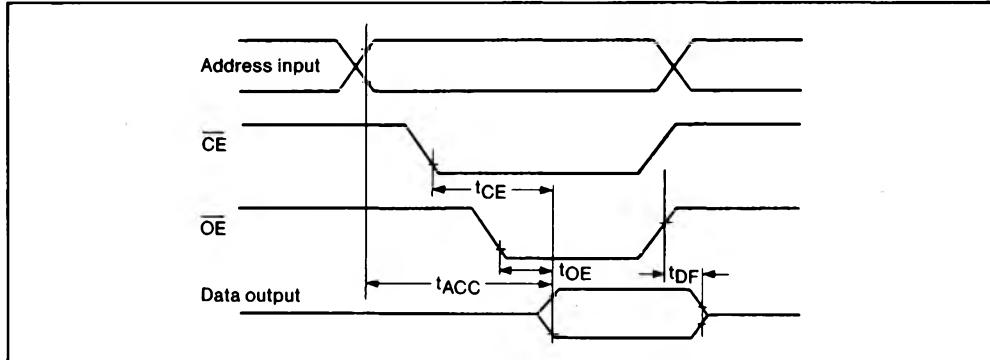
**AC CHARACTERISTICS**(V<sub>CC</sub> = 5V ± 5%, V<sub>PP</sub> = V<sub>CC</sub>, Ta = 0°C ~ 70°C)

Parameter	Symbol	Conditions	271024-12		271024-15		271024-20		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
Address Access Time	t <sub>ACC</sub>	CĒ = OĒ = V <sub>IL</sub> , PGM = V <sub>IH</sub>	—	120	—	150	—	200	ns
CĒ Access Time	t <sub>CE</sub>	OĒ = V <sub>IL</sub> , PGM = V <sub>IH</sub>	—	120	—	150	—	200	ns
OĒ Access Time	t <sub>OE</sub>	CĒ = V <sub>IL</sub> , PGM = V <sub>IH</sub>	—	50	—	60	—	75	ns
Output Disable Time	t <sub>DF</sub>	CĒ = V <sub>IL</sub> , PGM = V <sub>IH</sub>	0	40	0	50	0	55	ns

## Measurement condition

- Input pulse level ..... 0.45V and 2.4V
- Input timing reference level ..... 0.8V and 2.0V
- Output load ..... 1 TTL GATE + 100pF
- Output timing reference level ..... 0.8V and 2.0V

TIME CHART



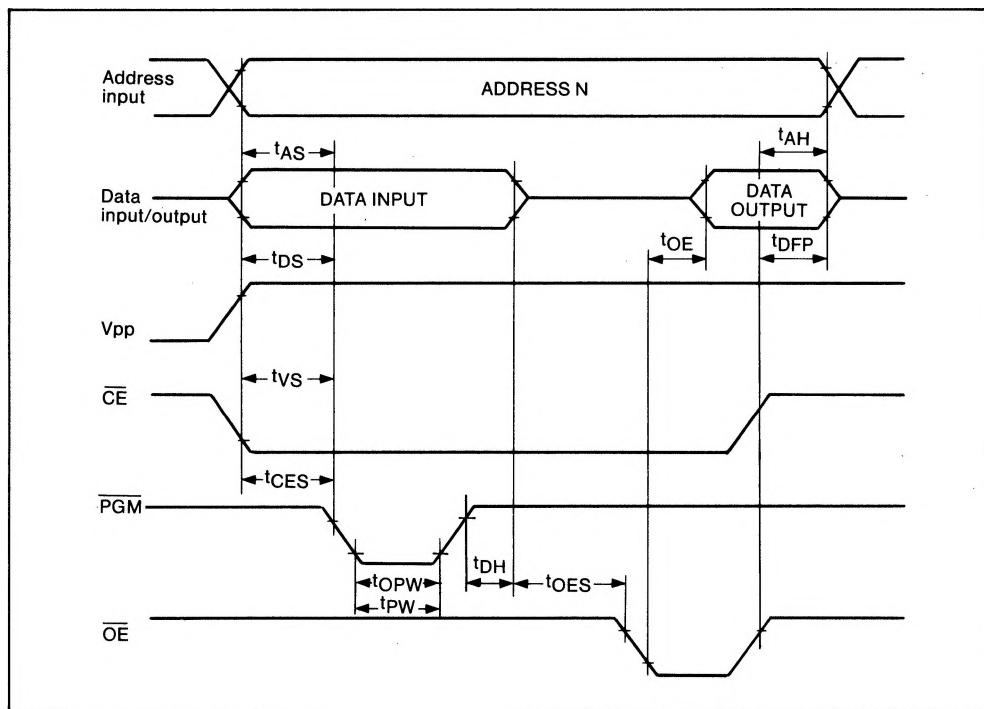
## &lt;PROGRAMMING OPERATION&gt;

**DC CHARACTERISTICS**(V<sub>CC</sub> = 6V ± 0.25V, V<sub>PP</sub> = 12.5V ± 0.5V, Ta = 25°C ± 5°C)

Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Input Leakage Current	I <sub>LI</sub>	V <sub>IN</sub> = 5.25V	—	—	10	µA
V <sub>PP</sub> Power Current	I <sub>PP</sub>	CE = PGM = V <sub>IL</sub>	—	—	50	mA
V <sub>CC</sub> Power Current	I <sub>CC</sub>	—	—	—	100	mA
Input Voltage "H" Level	V <sub>IH</sub>	—	2.0	—	V <sub>CC</sub> +1	V
Input Voltage "L" Level	V <sub>IL</sub>	—	-0.1	—	0.8	V
Output Voltage "H" Level	V <sub>OH</sub>	I <sub>OH</sub> = -400 µA	2.4	—	—	V
Output Voltage "L" Level	V <sub>OL</sub>	I <sub>OL</sub> = 2.1 mA	—	—	0.45	V

**AC CHARACTERISTICS**(V<sub>CC</sub> = 6V ± 0.25V, V<sub>PP</sub> = 12.5V ± 0.5V, Ta = 25°C ± 5°C)

Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Address Set-up Time	t <sub>AS</sub>	—	2	—	—	µs
OE Set-up Time	t <sub>OES</sub>	—	2	—	—	µs
Data Set-up Time	t <sub>DS</sub>	—	2	—	—	µs
Address Hold Time	t <sub>AH</sub>	—	0	—	—	µs
Data Hold Time	t <sub>DH</sub>	—	2	—	—	µs
Output Enable to Output Float Delay	t <sub>DFF</sub>	—	0	—	130	ns
V <sub>PP</sub> Power Set-up Time	t <sub>VS</sub>	—	2	—	—	µs
PGM Initial Program Pulse Width	t <sub>PW</sub>	—	0.95	1.0	1.05	ms
PGM Overprogram Pulse Width	t <sub>OPW</sub>	—	2.85	—	78.75	ms
CE Set-up Time	t <sub>CES</sub>	—	2	—	—	µs
Data Valid from OE	t <sub>OE</sub>	—	—	—	150	ns

**TIME CHART****CAPACITANCE**

(Ta = 25°C, f = 1 MHz)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> = 0V	-	4	6	pF
Output Capacitance	C <sub>OUT</sub>	V <sub>OUT</sub> = 0V	-	8	12	pF